

thermosetting polymer, fluoropolymer, thermoplastic polymer, polyimide, foams and combinations or composites thereof.

38. (Amended) The method according to Claim 35, further including the step of providing an encapsulant layer atop an exposed surface of said bond ribbons.

39. (Amended) The method according to Claim 38, wherein the encapsulant layer material is selected from the group consisting of silicone, flexibilized epoxy, thermoplastic and gel.

40. (Amended) The method according to Claim 38, further including the step of providing a second dielectric layer atop said encapsulant layer, wherein said second dielectric layer has a plurality of apertures for providing access to said terminals.

41. (Amended) The method according to Claim 35, wherein said dielectric layer is a silicon dioxide passivation layer provided on the contact bearing surface of said semiconductor chip.

42. (Amended) The method according to Claim 35, further including before providing the compliant layer, plating a barrier metal atop the contacts of said semiconductor chip, wherein said barrier metal reduces voiding at an interface between the contacts and said bond ribbons.

43. (Amended) The method according to Claim 35, wherein the method steps are applied simultaneously to a plurality of undiced semiconductor chips on a wafer to form a plurality of compliant semiconductor chip packages, the method further including dicing said wafer after selectively electroplating said bond ribbons to provide a plurality of individual compliant semiconductor chip packages.

44. (Amended) The method according to Claim 35, wherein the method steps are applied simultaneously to a plurality of adjacent semiconductor chips arranged in an array to form a plurality of compliant semiconductor chip packages, the method

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further including the step of dicing said adjacent packages after selectively electroplating said bond ribbons to provide a plurality of individual compliant semiconductor chip packages.

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48. (Amended) The method as claimed in claim 45, wherein said selectively forming bond ribbons step includes depositing a conductive material over the top of said package and etching away portions of said conductive material.
